

SPECIFICATION OF LED CHIP

C1200-30
[NIR]

1) Commodity Type and Physical Characteristics.

1. Material	InGaAsP/InP		
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern	Fig.1		
4. Chip Size	Fig.2		
5. Chip Thickness	Fig.2		
6. Emission Area	Fig.2		

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		0.95	1.20	V
		I _f =50mA		1.00	1.30	
Reverse Current	I _r	V _r =3V			10	uA
Power Intensity	P _o	I _f =20mA		1.6		mW
		I _f =50mA		3.3		
Wavelength	Peak	λ _P	1150	1200	1250	nm
	Centroid	λ _C		1190		
Spectral Radiation Bandwidth	Δλ	I _f =20mA		80		nm
RiseTime	t _r	I _f =20mA		25		ns
FallTime	t _f	I _f =20mA		20		ns

‡ Die shall be mounted on TO-18 gold header without resin coated.

‡ Power intensity is measured by PD G8370-85.

[Unit: um]

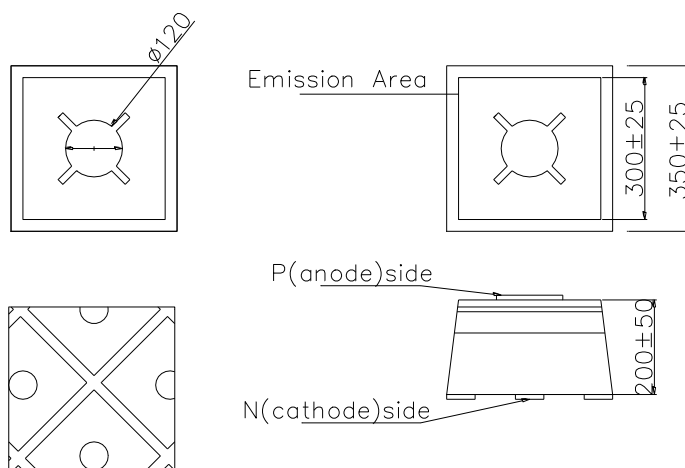


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area